

ABSTRACT OF THE DISCLOSURE

1 A semiconductor device is disclosed including a transistor that may have desired
2 characteristics due to a silicon nitride film that may prevent carbon from diffusing to a silicon
3 substrate. The semiconductor device (60) may include a device structure having an
4 insulating film formed from gas containing carbon. A silicon nitride film may be formed
5 between the insulating film and a transistor formation region in the silicon substrate for
6 preventing carbon from diffusing to the silicon substrate.